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Author Correction: Modulation of van der Waals and classical epitaxy induced by strain at the Si step edges in GeSbTe alloys

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This Article contains errors in Figure 4b. The colours of the curves in the left panel were inadvertently switched. The correct Figure 4b appears below as Figure 1.

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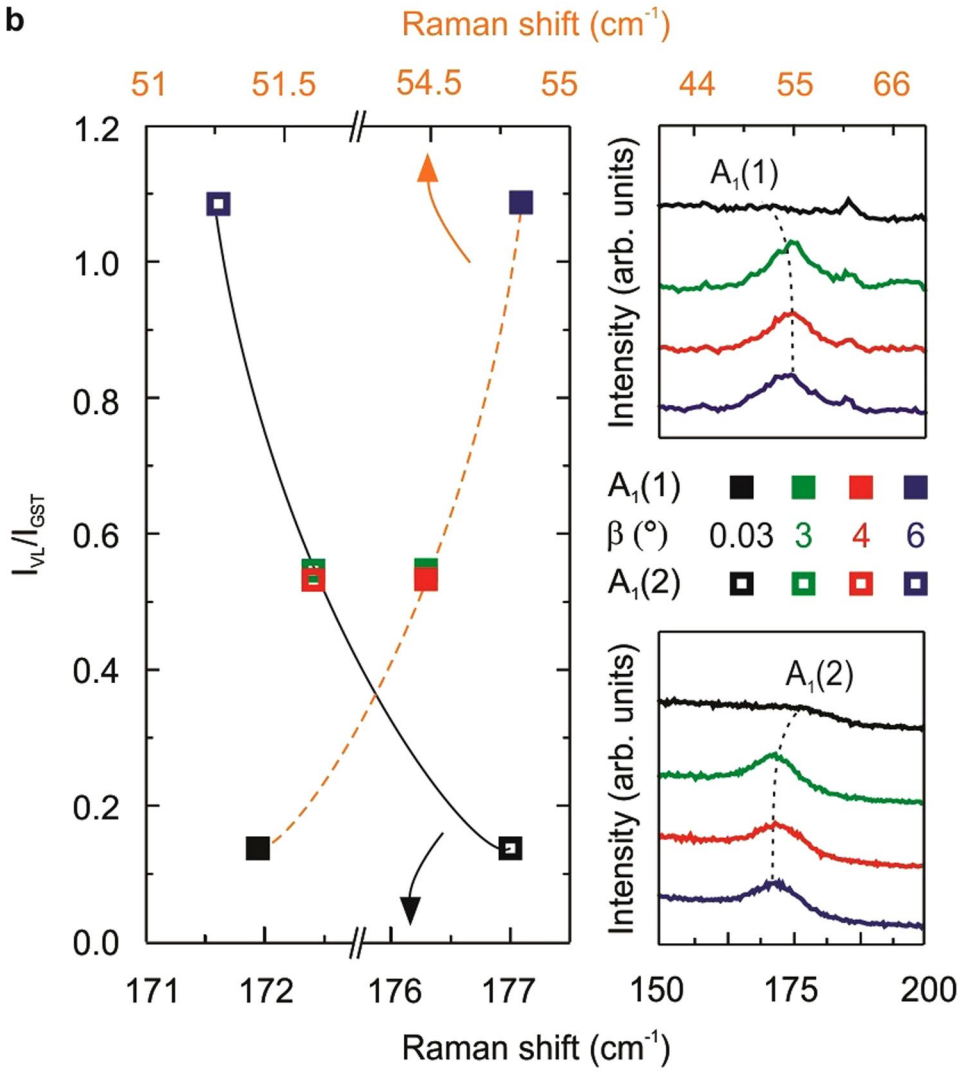

Figure 1. Stable rhombohedral stacking with almost pure GST124 on substrate miscut. (**a**) Raman spectra of 70 nm-thick GST grown on Si (111) with $\beta = 0.03°$ at RT (black), $\beta = 4°$ at RT (red) and $\beta = 4°$ at 10 K (dark red). (**b**) Intensity ratio of the second order XRD for the VL peak and GST peak (IVL/IGST) as a function of the Raman shift for the $A_1(1)$ (full squares) and $A_1(2)$ (empty squares) modes with $\beta = 0.03°$ (black), 3° (green), 4° (red) and 6° (blue). Dashed and solid lines serve as a guide to the eye. The top and bottom right panels show the Raman shift of the $A_1(1)$ and $A_1(2)$ modes, respectively. (**c**) 70 nm- (red) or 7 nm- (light blue) thick GST grown on Si (111) with $\beta = 4°$.